

Low temperature PEALD of epitaxial AlN on GaN, Ga₂O₃, and Al₂O₃ surfaces

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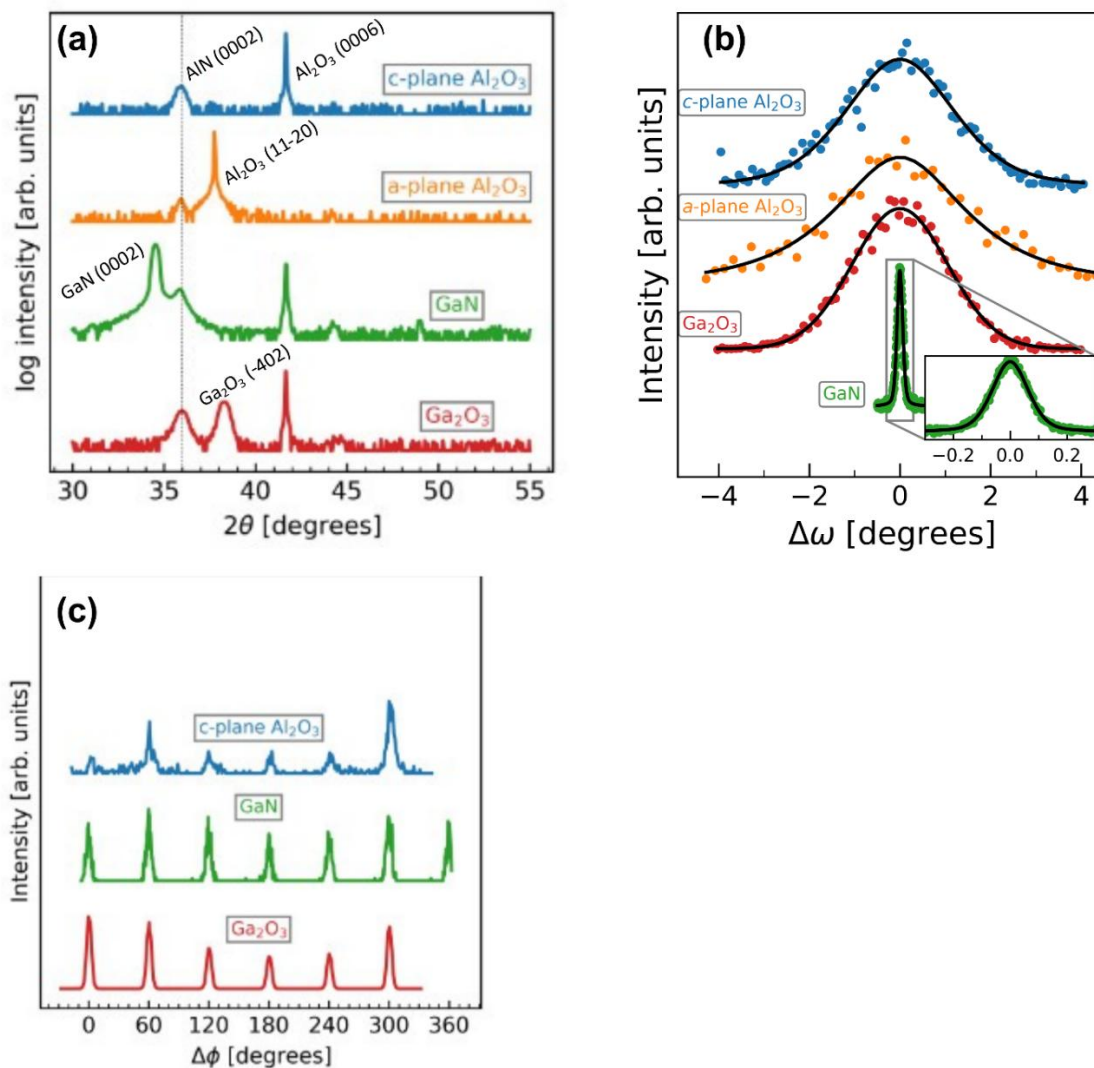


Figure 1. (a) On-axis high resolution x-ray diffraction (HRXRD) 2θ/ω scans of AlN films on various substrates and templates, with AlN (0002) peak indicated by dashed black line. (b) HRXRD ω rocking curve measurement at the AlN (0002) peak. (c) In-plane grazing incidence diffraction (IP-GID) long range φ scans at the AlN (11-20) peak showing 60 degree azimuthal rotational symmetry.